



# P-Channel 1.5 V (G-S) MOSFET

PRODUCT SUMMARY						
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)			
	$0.023$ at $V_{GS} = -4.5 \text{ V}$	- 7				
- 8	0.029 at $V_{GS} = -2.5 \text{ V}$	- 6.2	28			
- 0	0.036 at V <sub>GS</sub> = - 1.8 V	- 5.2	20			
	0.048 at V <sub>GS</sub> = - 1.5 V	- 5				

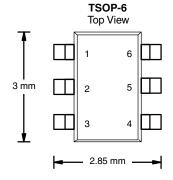
### **FEATURES**

- Halogen-free According to IEC 61249-2-21
- TrenchFET® Power MOSFET: 1.5 V Rated
- Ultra-Low On-Resistance
- 100 % R<sub>q</sub> Tested
- Compliant to RoHS Directive 2002/95/EC



#### **APPLICATIONS**

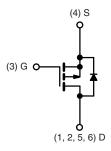
• Load Switch for Portable Devices



Ordering Information: Si3499DV-T1-E3 (Lead (Pb)-free)

Si3499DV-T1-GE3 (Lead (Pb)-free and Halogen-free)

Marking Code: 99xxx



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	, ( · A = 5 0, arms			011-01-1-	1114
Parameter		Symbol	5 s	Steady State	Unit
Drain-Source Voltage		$V_{DS}$	- 8		V
Gate-Source Voltage		$V_{GS}$	± 5		
Continuous Dunin Courset /T 150 °C\2	T <sub>A</sub> = 25 °C	I <sub>D</sub>	- 7	- 5.3	^
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 85 °C		- 3.6	- 3.9	
Pulsed Drain Current		I <sub>DM</sub>	- 20		Α
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	- 1.7	- 0.9	
	T <sub>A</sub> = 25 °C	P <sub>D</sub>	2	1.1	W
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 85 °C		1	0.6	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stq</sub>	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Marrian Institut to Ambiguit	t ≤ 5 s	R <sub>thJA</sub>	45	62.5	°C/W
Maximum Junction-to-Ambient <sup>a</sup>	Steady State	' 'thJA	90	110	
Maximum Junction-to-Foot (Drain)	Steady State	R <sub>thJF</sub>	25	30	

a. Surface mounted on 1" x 1" FR4 board.

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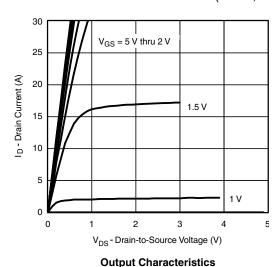
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 0.35		- 0.75	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 5 \text{ V}$			± 100	nA	
Zava Cata Valtaga Drain Current	1	V <sub>DS</sub> = -8 V, V <sub>GS</sub> = 0 V			- 1	μΑ	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = - 8 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 85 °C			- 10		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = - 5 V, V <sub>GS</sub> = - 4.5 V	- 20			Α	
		V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 7 A		0.019	0.023		
		$V_{GS} = -2.5 \text{ V}, I_D = -6.2 \text{ A}$		0.024	0.029	0	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 1.8 V, I <sub>D</sub> = - 5.2 A		0.028	0.036	Ω	
		V <sub>GS</sub> = - 1.5 V, I <sub>D</sub> = - 3 A		0.035	0.048		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 5 V, I <sub>D</sub> = - 7 A		28		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>S</sub> = - 1.7 A, V <sub>GS</sub> = 0 V		- 0.63	- 1.1	V	
Dynamic <sup>b</sup>							
Total Gate Charge	$Q_g$			28	42		
Gate-Source Charge	$Q_{gs}$	$V_{DS}$ = - 4 V, $V_{GS}$ = - 4.5 V, $I_D$ = - 7 A		2.9		nC	
Gate-Drain Charge	$Q_{gd}$			5.8			
Gate Resistance	$R_{g}$		4	8.5	13	Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			27	40		
Rise Time	t <sub>r</sub>	$V_{DD} = -4 \text{ V}, R_L = 4 \Omega$		65	100		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong$ - 1 A, $V_{GEN}$ = - 4.5 V, $R_g$ = 6 $\Omega$		210	315	ns	
Fall Time	t <sub>f</sub>			110	165		
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>E</sub> = - 1.7 A, dI/dt = 100 A/μs		40	70		

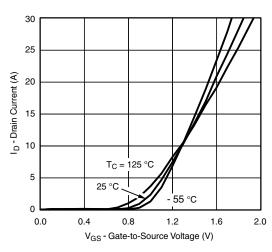
### Notes:

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
  b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

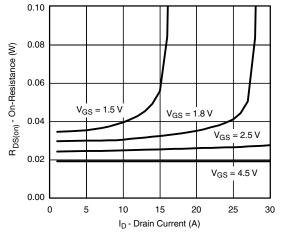




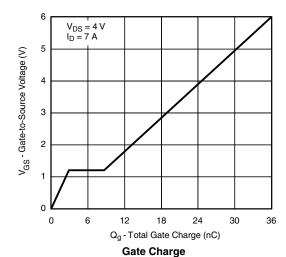
**Transfer Characteristics** 

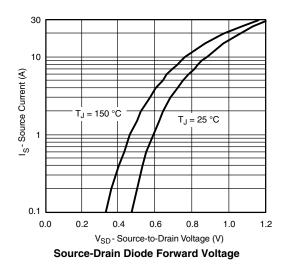


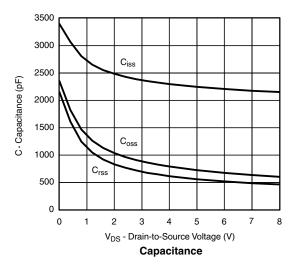
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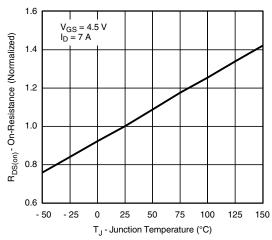


#### On-Resistance vs. Drain Current

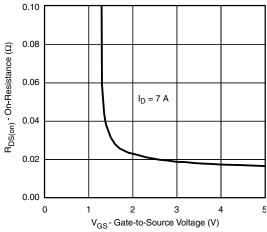








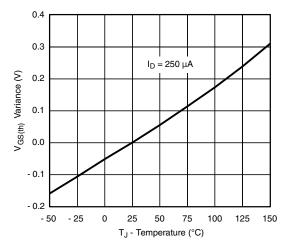
On-Resistance vs. Junction Temperature

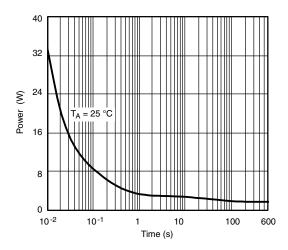


On-Resistance vs. Gate-to-Source Voltage

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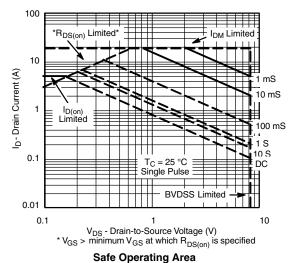
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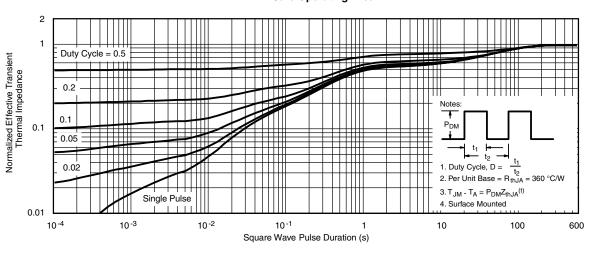




#### **Threshold Voltage**



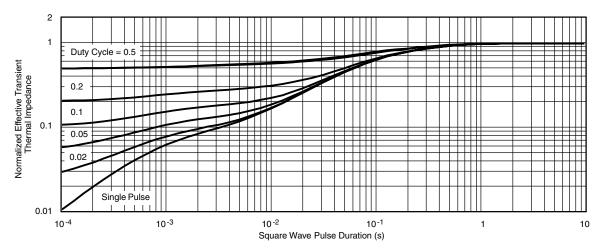




Normalized Thermal Transient Impedance, Junction-to-Ambient

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### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?73138.

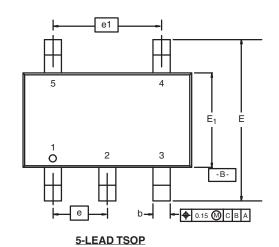
Document Number: 73138 S11-1140-Rev. C, 13-Jun-11

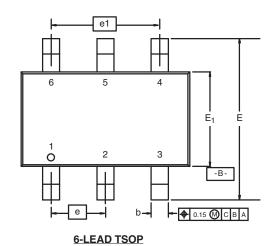


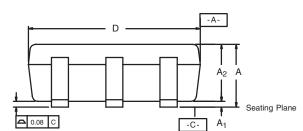


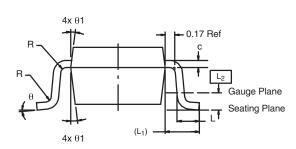
TSOP: 5/6-LEAD

**JEDEC Part Number: MO-193C** 







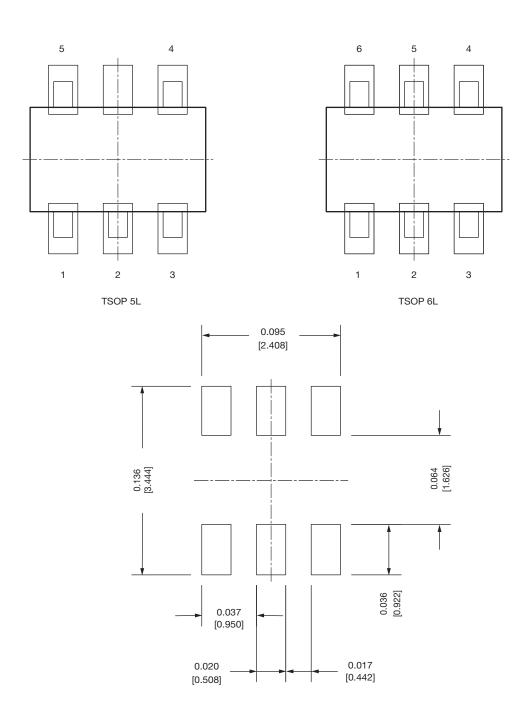


	MIL	LIMETER	RS	INCHES			
Dim	Min	Nom	Max	Min	Nom	Max	
Α	0.91	-	1.10	0.036	-	0.043	
A <sub>1</sub>	0.01	-	0.10	0.0004	-	0.004	
A <sub>2</sub>	0.90	-	1.00	0.035	0.038	0.039	
b	0.30	0.32	0.45	0.012	0.013	0.018	
С	0.10	0.15	0.20	0.004	0.006	0.008	
D	2.95	3.05	3.10	0.116	0.120	0.122	
E	2.70	2.85	2.98	0.106	0.112	0.117	
E <sub>1</sub>	1.55	1.65	1.70	0.061	0.065	0.067	
е	0.95 BSC			0.0374 BSC			
e <sub>1</sub>	1.80	1.90	2.00	0.071	0.079		
L	0.32	-	0.50	0.012	-	0.020	
L <sub>1</sub>	0.60 Ref			0.024 Ref			
L <sub>2</sub>	0.25 BSC			0.010 BSC			
R	0.10	-	-	0.004	-	-	
θ	0°	4°	8°	0°	4°	8°	
$\theta_1$		7° Nom		7° Nom			
ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540							

Document Number: 71200 www.vishay.com 18-Dec-06



# Recommended Land Pattern For TSOP-5L / TSOP-6L



### Note

• All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022 DWG: 3010



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